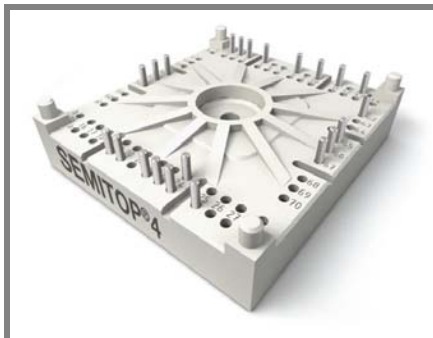


SK75GD126T



SEMITOP® 4

IGBT Module

SK75GD126T

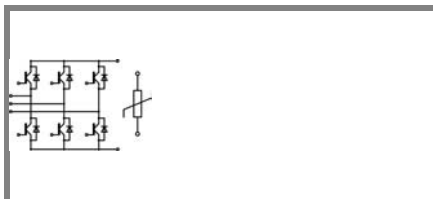
Preliminary Data

Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

- Inverter up to 42 kVA
- Typ. motor power 18,5 kW

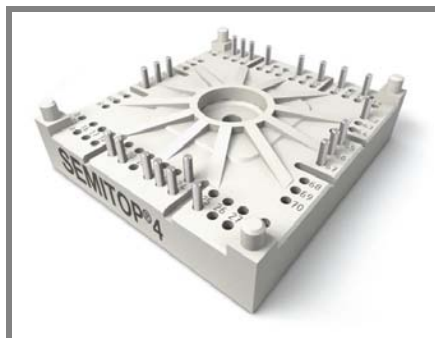


GD-T

Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}	$T_j = 25\text{ °C}$	1200		V
I_C	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$	88	A
		$T_s = 70\text{ °C}$	67	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	140		A
V_{GES}		± 20		V
t_{psc}	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125\text{ °C}$ $V_{CES} < 1200\text{ V}$	10		µs
Inverse Diode				
I_F	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$	91	A
		$T_s = 70\text{ °C}$	68	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	150		A
Module				
$I_{t(RMS)}$				A
T_{vj}		-40 ... +150		°C
T_{stg}		-40 ... +125		°C
V_{isol}	AC, 1 min.	2500		V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 3\text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	$T_j = 25\text{ °C}$	0,0094		mA
		$T_j = 125\text{ °C}$			mA
I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$	$T_j = 25\text{ °C}$	1200		nA
		$T_j = 125\text{ °C}$			nA
V_{CE0}		$T_j = 25\text{ °C}$	1	1,2	V
		$T_j = 125\text{ °C}$	0,9	1,1	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	10	13	mΩ
		$T_j = 125\text{ °C}$	16	19	mΩ
$V_{CE(sat)}$	$I_{Cnom} = 75\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{chiplev.}$	1,7	2,1	V
		$T_j = 125\text{ °C}_{chiplev.}$	2	2,4	V
C_{ies}	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	5		nF
C_{oes}			0,26		nF
C_{res}			0,23		nF
$t_{d(on)}$	$R_{Gon} = 8,2\ \Omega$ $di/dt = 1340\text{ A}/\mu\text{s}$	$V_{CC} = 600\text{ V}$ $I_C = 75\text{ A}$	62		ns
t_r			32		ns
E_{on}	$R_{Goff} = 8,2\ \Omega$ $di/dt = 1340\text{ A}/\mu\text{s}$	$T_j = 125\text{ °C}$ $V_{GE} = -7/+15\text{ V}$	11,3		mJ
$t_{d(off)}$			514		ns
t_f			90		ns
E_{off}			10		mJ
$R_{th(j-s)}$	per IGBT	0,5		K/W	

SK75GD126T



SEMITOP® 4

IGBT Module

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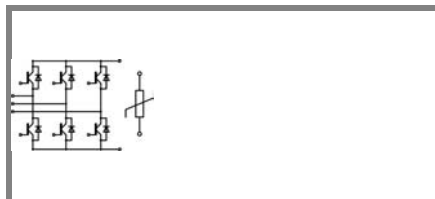
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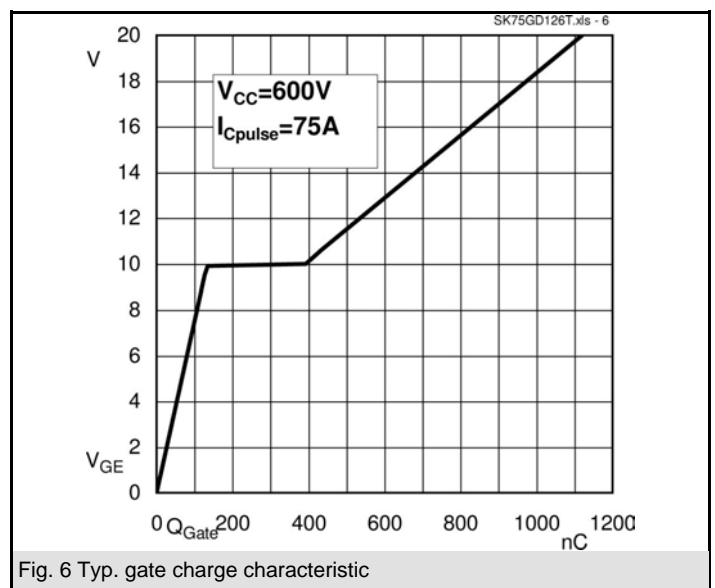
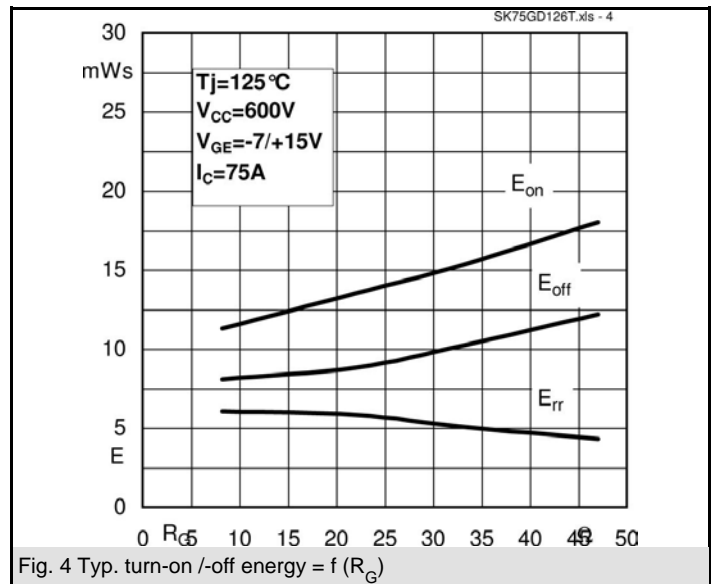
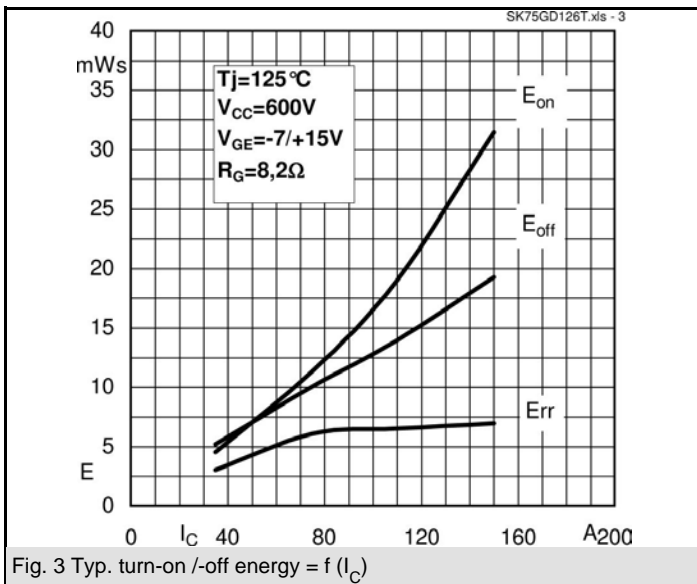
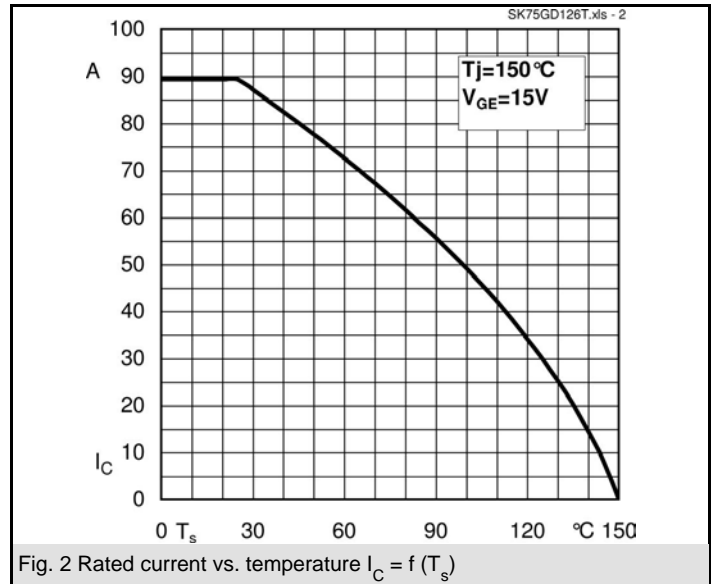
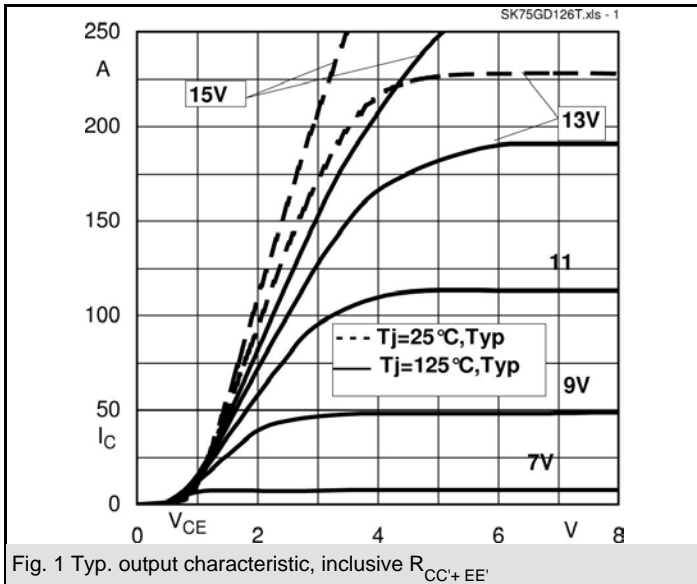
GD-T

Characteristics

Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 75 \text{ A}; V_{GE} = 0 \text{ V}$		$T_j = 25 \text{ }^\circ\text{C}_{\text{chiplev.}}$	1,46	V
			$T_j = 125 \text{ }^\circ\text{C}_{\text{chiplev.}}$	1,4	V
V_{F0}			$T_j = 25 \text{ }^\circ\text{C}$	1,05	V
			$T_j = 125 \text{ }^\circ\text{C}$	0,95	V
r_F			$T_j = 25 \text{ }^\circ\text{C}$	5,5	mΩ
			$T_j = 125 \text{ }^\circ\text{C}$	6	mΩ
I_{RRM}	$I_F = 75 \text{ A}$	$T_j = 125 \text{ }^\circ\text{C}$	70		A
Q_{rr}	$di/dt = 1340 \text{ A}/\mu\text{s}$		20		μC
E_{rr}	$V_{CC} = 600\text{V}$		6		mJ
$R_{th(j-s)D}$	per diode		0,7		K/W
M_s	to heat sink	2,5		2,75	Nm
w			60		g
Temperature sensor					
R_{100}	$T_s = 100^\circ\text{C} (R_{25} = 5\text{k}\Omega)$		493±5%		Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



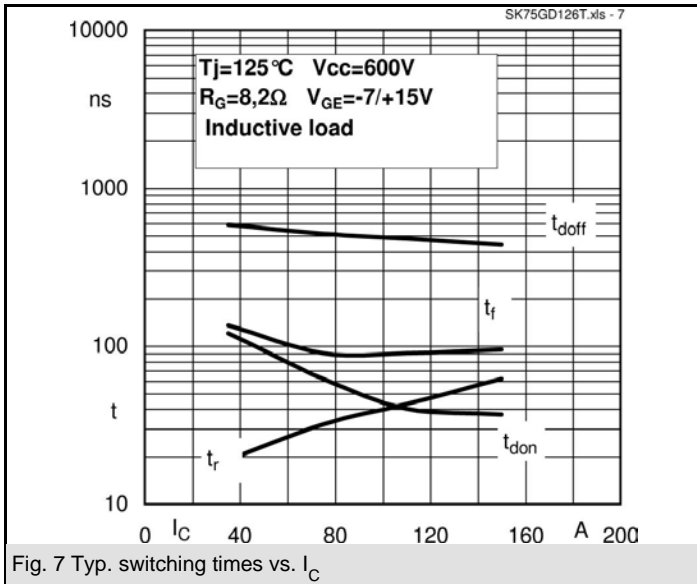


Fig. 7 Typ. switching times vs. I_C

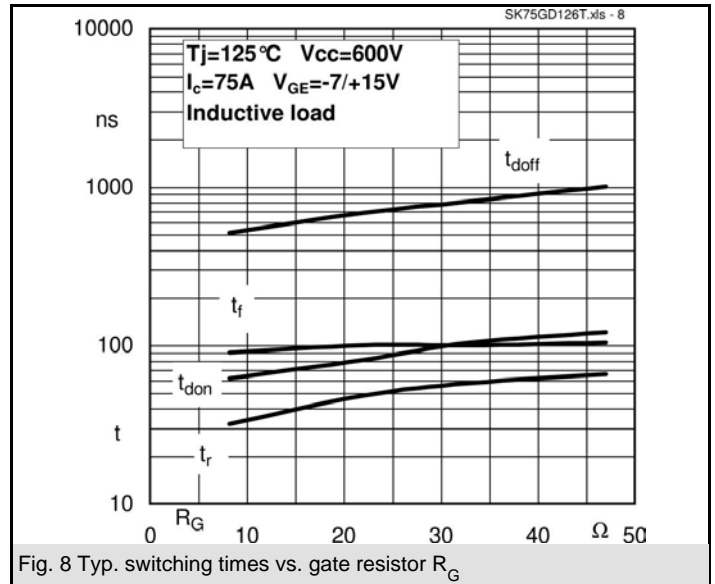


Fig. 8 Typ. switching times vs. gate resistor R_G

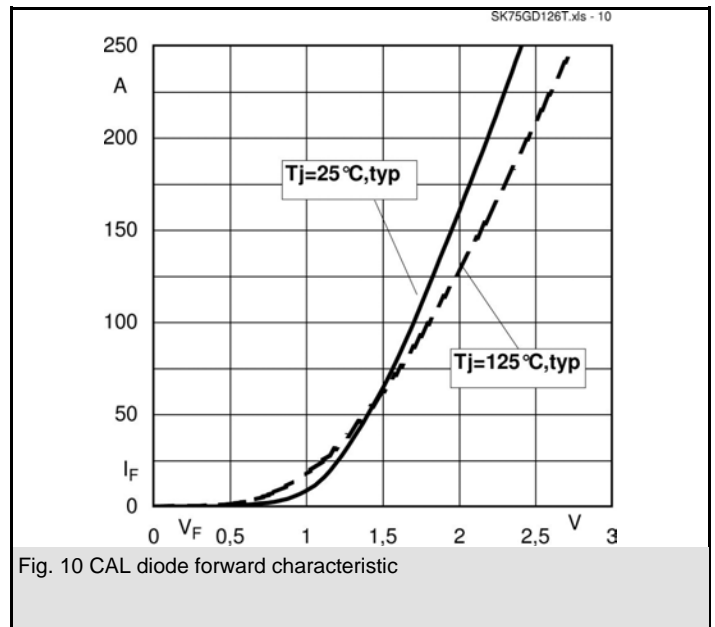


Fig. 10 CAL diode forward characteristic

